

Top View

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Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	100
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0034
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0040
I _D (A)	135
Configuration	Single
Package	PowerPAK 8 x 8L

PowerPAK® 8 x 8L Single One of the state of

Bottom View

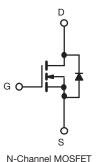
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Fully lead (Pb)-free device
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ROHS COMPLIANT HALOGEN FREE



PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	100	V	
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current	T _C = 25 °C	1	135		
	T _C = 125 °C	Ι _D	78		
Continuous Source Current (Diode Conduction)		I _S	124	А	
Pulsed Drain Current ^a		I _{DM}	210		
Single Pulse Avalanche Current	Current		68		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	231	mJ	
Maximum Power Dissipation	T _C = 25 °C		136	W	
	T _C = 125 °C	P_{D}	45		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175		
Soldering Recommendations (Peak Temperature) c, d		•	260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount b	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.1	C/VV

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. When mounted on 1" square PCB (FR4 material).
- c. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		100	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2	2.5] v
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 100 V	-	-	1	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0 V$	$V_{DS} = 100 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	ı	-	50	μΑ
		$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 175 °C	1	-	500	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
Drain-Source On-State Resistance a		V _{GS} = 10 V	I _D = 20 A	ı	0.0028	0.0034	Ω
	D	$V_{GS} = 4.5 \text{ V}$	I _D = 10 A	1	0.0033	0.0040	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	ı	-	0.0058	
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0074	1
Forward Transconductance b	9fs	V _{DS} = 15 V, I _D = 15 A		-	84	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	5620	7350	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	2850	3750	pF
Reverse Transfer Capacitance	C _{rss}			-	220	290	1
Total Gate Charge ^c	Qg			-	97	150	
Gate-Source Charge c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_D = 10 \text{ A}$	-	15	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	20	-	
Gate Resistance	R_g	f = 1 MHz		0.95	1.92	3	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	19	30	
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, R_L = 5 \Omega$ $I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	40	60	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	69	110	
Fall Time ^c	t _f			-	87	135	
Source-Drain Diode Ratings and Cha	racteristics b						
Pulsed Current ^a	I _{SM}			-	-	210	Α
		ł					V

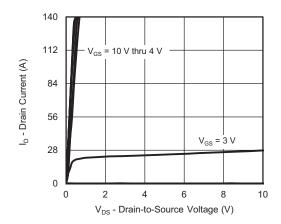
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

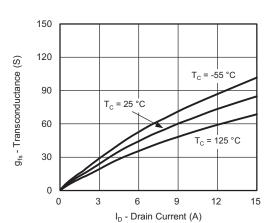
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



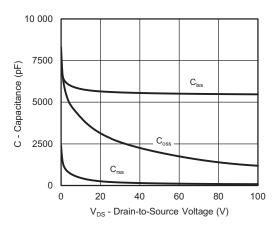
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



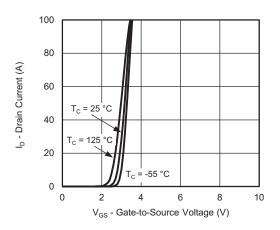
Output Characteristics



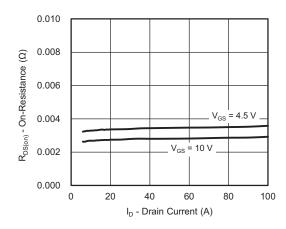
Transconductance



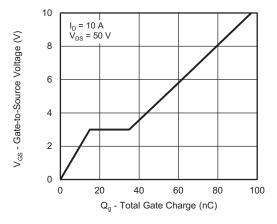
Capacitance



Transfer Characteristics



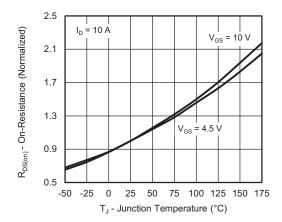
On-Resistance vs. Drain Current



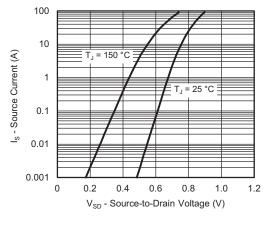
Gate Charge



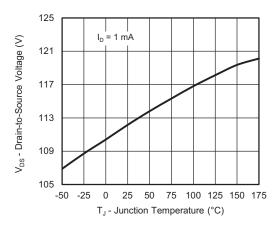
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



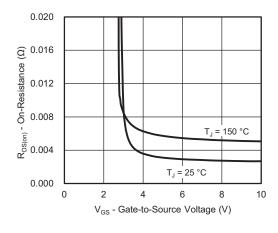
On-Resistance vs. Junction Temperature



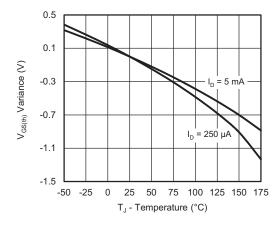
Source Drain Diode Forward Voltage



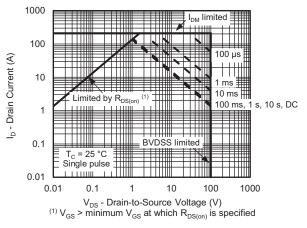
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



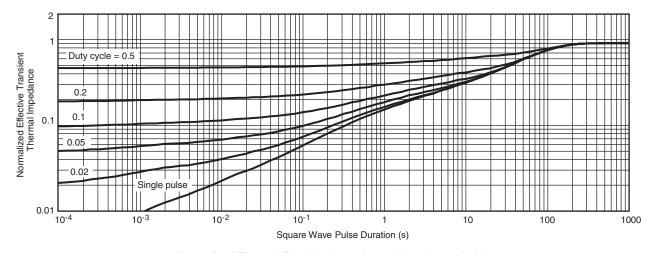
Threshold Voltage



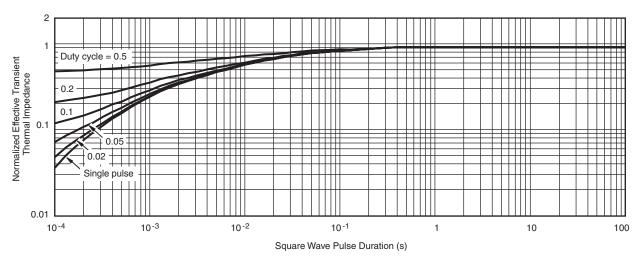
Safe Operating Area



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



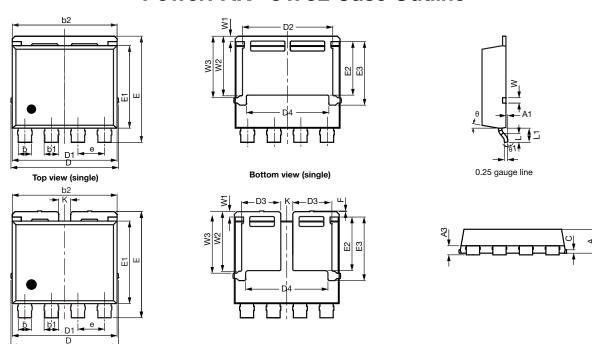
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?76643.



Top view (dual)

PowerPAK® 8 x 8L Case Outline



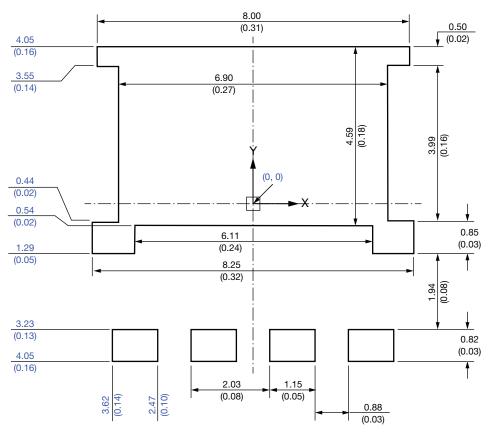
Bottom view (dual)

DIM		MILLIMETERS		INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	1.70	1.80	1.90	0.067	0.071	0.075
A1	0.00	0.08	0.13	0.000	0.003	0.005
A3	0.55	0.62	0.70	0.022	0.024	0.028
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	7.80	7.90	8.00	0.307	0.311	0.315
С	0.20	0.25	0.30	0.008	0.010	0.012
D	8.00	8.10	8.25	0.315	0.319	0.325
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D3	2.85	2.95	3.05	0.112	0.116	0.120
D4	6.11	6.21	6.31	0.241	0.244	0.248
е	1.95	2.00	2.05	0.077	0.079	0.081
E	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	3.94	4.04	4.14	0.140	0.159	0.163
E3	4.69	4.79	4.89	0.185	0.189	0.193
F	0.05	0.10	0.15	0.002	0.004	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.80	0.90	1.00	0.031	0.035	0.039
W	0.30	0.40	0.50	0.012	0.016	0.020
W1	0.30	0.40	0.50	0.012	0.016	0.020
W2	4.39	4.49	4.59	0.173	0.177	0.181
W3	4.54	4.64	4.74	0.179	0.183	0.187
θ	6°	10°	14°	6°	10°	14°
θ1	0°	3°	8°	0°	3°	8°
θ1 -0891-Rev. A, G: 6026	ŭ	3°	8°	0°	3°	

Revision: 06-Oct-14 1 Document Number: 67734



Recommended Minimum PADs for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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